

MITSUBISHI IGBT MODULES  
**CM100RL-12NF**

HIGH POWER SWITCHING USE

**CM100RL-12NF**



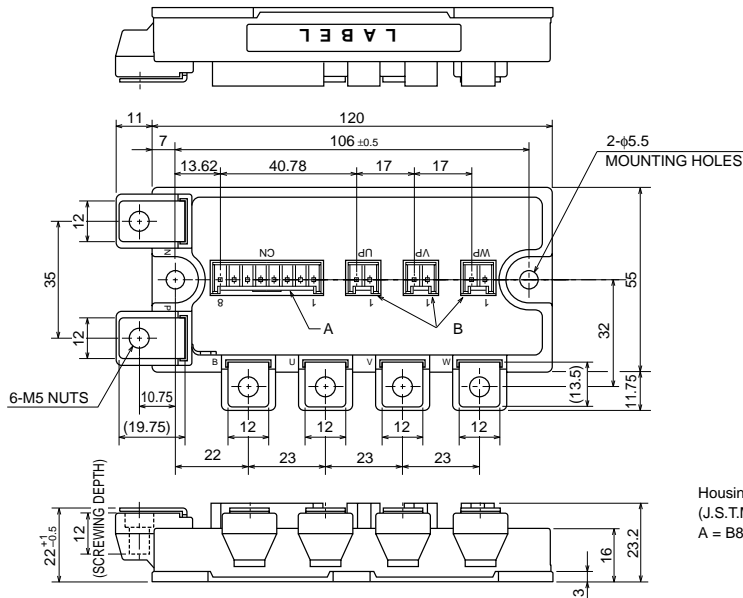
- IC ..... 100A
- VCES ..... 600V
- Insulated Type
- 7-elements in a pack

**APPLICATION**

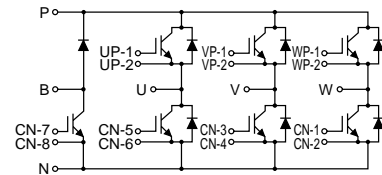
AC drive inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



Housing Type of A and B  
 (J.S.T.Mfg.Co.Ltd)  
 A = B8P-VH-FB-B, B = B2P-VH-FB-B



**CIRCUIT DIAGRAM**

## CM100RL-12NF

## HIGH POWER SWITCHING USE

ABSOLUTE MAXIMUM RATINGS ( $T_j = 25^\circ\text{C}$ )

## INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	600	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>c</sub> = 99°C <sup>*1</sup>	100	A
I <sub>CM</sub>		Pulse (Note 2)	200	A
I <sub>E</sub> (Note 1)	Emitter current		100	A
I <sub>EM</sub> (Note 1)		Pulse (Note 2)	200	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>c</sub> = 25°C	540	W

## BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	600	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>c</sub> = 107°C <sup>*1</sup>	50	A
I <sub>CM</sub>		Pulse (Note 2)	100	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>c</sub> = 25°C	320	W
V <sub>RRM</sub>	Repetitive peak reverse voltage	Clamp diode part	600	V
I <sub>FM</sub>	Forward current	Clamp diode part	50	A

## (COMMON RATING)

Symbol	Parameter	Conditions	Ratings	Unit
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>iso</sub>	Isolation voltage	Main Terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M5	2.5 ~ 3.5	N • m
—		Mounting holes M5	2.5 ~ 3.5	N • m
—	Weight	Typical value	350	g

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C)**  
**INVERTER PART**

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA	
VGE(th)	Gate-emitter threshold voltage	IC = 10mA, VCE = 10V	6	7	8	V	
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA	
VCE(sat)	Collector-emitter saturation voltage	IC = 100A, VGE = 15V	T <sub>j</sub> = 25°C	—	1.7	2.2	V
			T <sub>j</sub> = 125°C	—	1.7	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	15	nF	
Coes	Output capacitance		—	—	1.9	nF	
Cres	Reverse transfer capacitance		—	—	0.6	nF	
QG	Total gate charge	VCC = 300V, IC = 100A, VGE = 15V	—	400	—	nC	
td(on)	Turn-on delay time	VCC = 300V, IC = 100A VGE1 = VGE2 = 15V RG = 6.3Ω, Inductive load switching operation IE = 100A	—	—	120	ns	
tr	Turn-on rise time		—	—	100	ns	
td(off)	Turn-off delay time		—	—	300	ns	
tf	Turn-off fall time		—	—	300	ns	
trr (Note 1)	Reverse recovery time		—	—	120	ns	
Qrr (Note 1)	Reverse recovery charge	—	2.1	—	μC		
VEC(Note 1)	Emitter-collector voltage	IE = 100A, VGE = 0V	—	—	2.8	V	
Rth(j-c)Q	Thermal resistance	IGBT part (1/6 module) <sup>*1</sup>	—	—	0.23	°C/W	
Rth(j-c)R		FWDi part (1/6 module) <sup>*1</sup>	—	—	0.41	°C/W	
Rth(c-f)	Contact thermal resistance	Case to fin, Thermal compound Applied (1/6 module) <sup>*2</sup>	—	0.085	—	°C/W	
RG	External gate resistance		6.3	—	63	Ω	

**BRAKE PART**

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA	
VGE(th)	Gate-emitter threshold voltage	IC = 5.0mA	6	7	8	V	
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA	
VCE(sat)	Collector-emitter saturation voltage	IC = 50A, VGE = 15V	T <sub>j</sub> = 25°C	—	1.7	2.2	V
			T <sub>j</sub> = 125°C	—	1.7	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	7.5	nF	
Coes	Output capacitance		—	—	1.0	nF	
Cres	Reverse transfer capacitance		—	—	0.3	nF	
QG	Total gate charge	VCC = 300V, IC = 50A, VGE = 15V	—	200	—	nC	
VFM	Forward voltage drop	IF = 50A	—	—	2.8	V	
Rth(j-c)Q	Thermal resistance	IGBT part <sup>*1</sup>	—	—	0.39	°C/W	
Rth(j-c)R		Clamp diode part <sup>*1</sup>	—	—	0.70	°C/W	
RG	External gate resistance		13	—	130	Ω	

\*1 : T<sub>c</sub> measured point is just under the chips.

If you use this value, Rth(i-a) should be measured just under the chips.

\*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

Note 1. IE, VEC, trr & Qrr represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

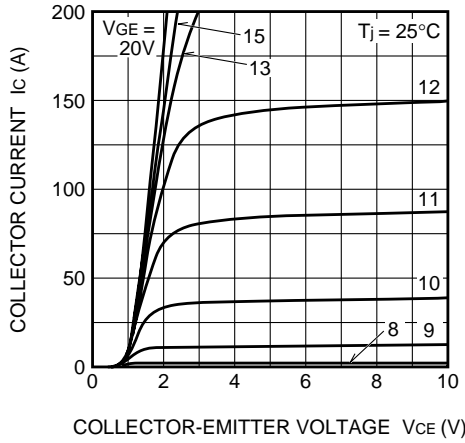
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

# CM100RL-12NF

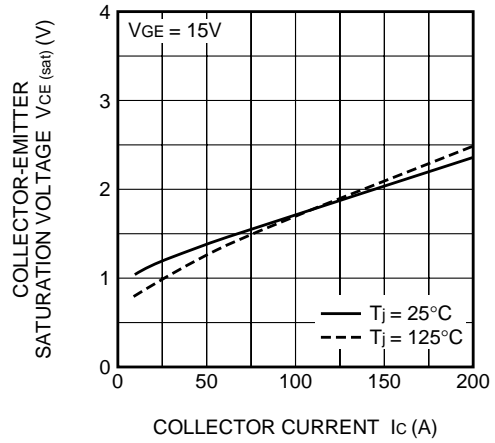
HIGH POWER SWITCHING USE

## PERFORMANCE CURVES

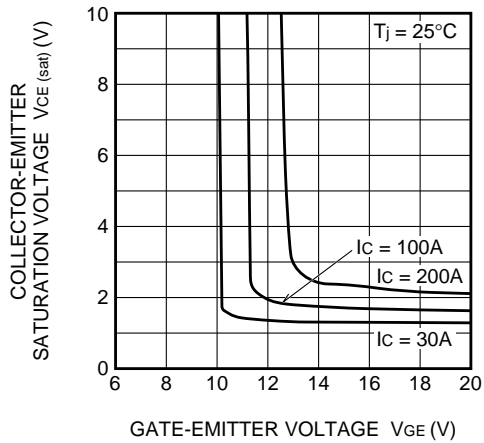
**OUTPUT CHARACTERISTICS (TYPICAL)**



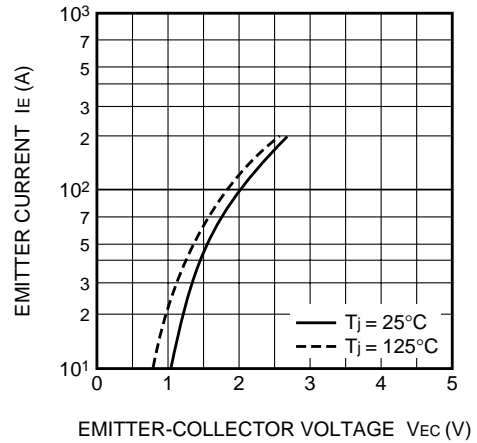
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



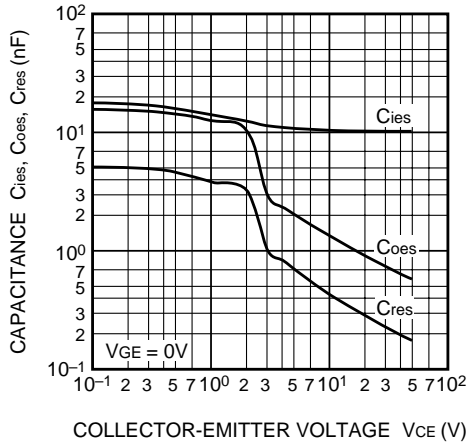
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



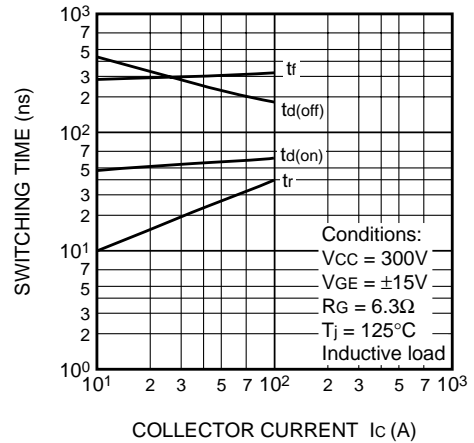
**FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**



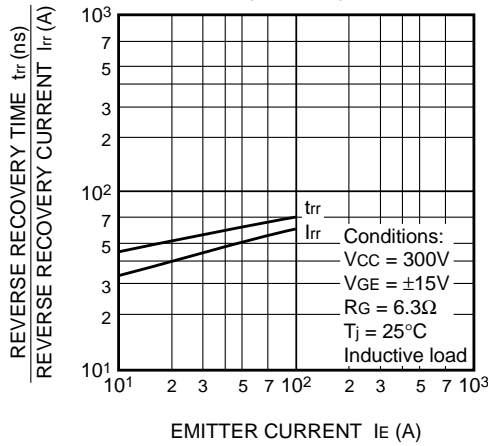
**CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)**



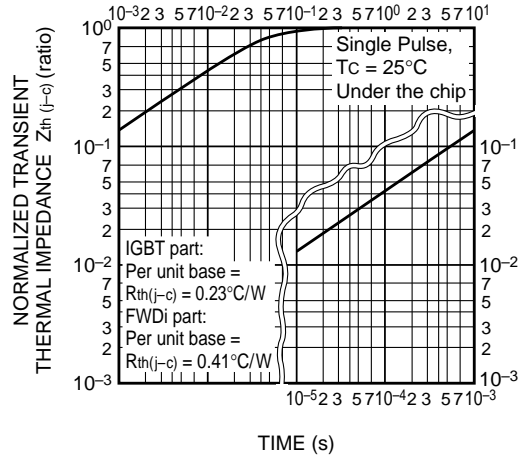
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**



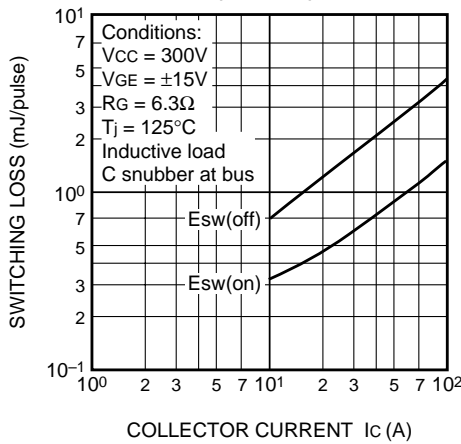
REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



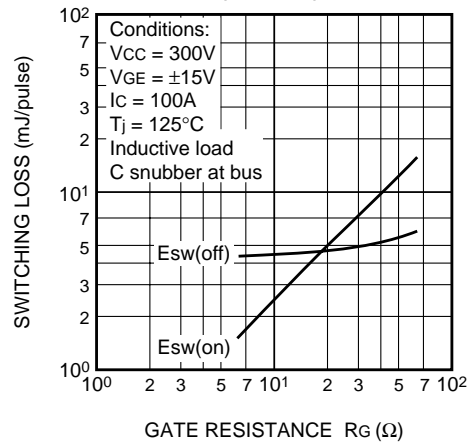
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



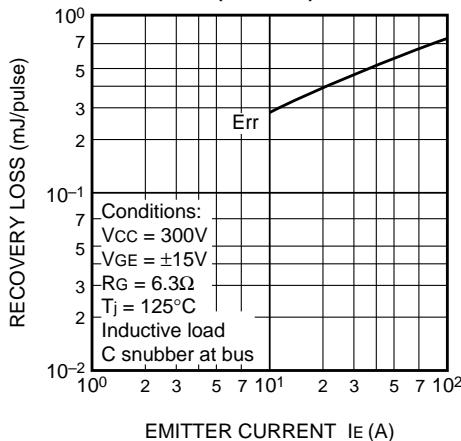
SWITCHING LOSS vs. COLLECTOR CURRENT (TYPICAL)



SWITCHING LOSS vs. GATE RESISTANCE (TYPICAL)



RECOVERY LOSS vs. IE (TYPICAL)



RECOVERY LOSS vs. GATE RESISTANCE (TYPICAL)

